

# Chen Li

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8522292/publications.pdf>

Version: 2024-02-01

13  
papers

534  
citations

933447

10  
h-index

1125743

13  
g-index

13  
all docs

13  
docs citations

13  
times ranked

352  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of nonvertical ion bombardment due to edge effects on polymer surface morphology evolution and etching uniformity. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	2.1	1
2	Etching of Si <sub>3</sub> N <sub>4</sub> induced by electron beam plasma from hollow cathode plasma in a downstream reactive environment. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020, 38, 032208.	1.2	3
3	Electron beam injection from a hollow cathode plasma into a downstream reactive environment: Characterization of secondary plasma production and Si <sub>3</sub> N <sub>4</sub> and Si etching. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, 033001.	2.1	5
4	Selective atomic layer etching of HfO <sub>2</sub> over silicon by precursor and substrate-dependent selective deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, .	2.1	16
5	Achieving ultrahigh etching selectivity of SiO <sub>2</sub> over Si <sub>3</sub> N <sub>4</sub> and Si in atomic layer etching by exploiting chemistry of complex hydrofluorocarbon precursors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018, 36, .	2.1	40
6	Characterizing fluorocarbon assisted atomic layer etching of Si using cyclic Ar/C <sub>4</sub> F <sub>8</sub> and Ar/CHF <sub>3</sub> plasma. <i>Journal of Chemical Physics</i> , 2017, 146, 052801.	3.0	35
7	Investigation of thin oxide layer removal from Si substrates using an SiO <sub>2</sub> atomic layer etching approach: the importance of the reactivity of the substrate. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 254006.	2.8	24
8	Application of cyclic fluorocarbon/argon discharges to device patterning. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, .	2.1	17
9	Impact of hydrofluorocarbon molecular structure parameters on plasma etching of ultra-low-K dielectric. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, .	2.1	18
10	Fluorocarbon based atomic layer etching of Si <sub>3</sub> N <sub>4</sub> and etching selectivity of SiO <sub>2</sub> over Si <sub>3</sub> N <sub>4</sub> . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, .	2.1	75
11	Effect of the chamber wall on fluorocarbon-assisted atomic layer etching of SiO <sub>2</sub> using cyclic Ar/C <sub>4</sub> F <sub>8</sub> plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, 040603.	2.1	24
12	Fluorocarbon assisted atomic layer etching of SiO <sub>2</sub> and Si using cyclic Ar/C <sub>4</sub> F <sub>8</sub> and Ar/CHF <sub>3</sub> plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, .	2.1	74
13	Atomic Layer Etching at the Tipping Point: An Overview. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, N5041-N5053.	1.8	202